

The documentation and process conversion measures necessary to comply with this revision shall be completed by 19 May 2003.

INCH-POUND

MIL-PRF-19500/577B  
 19 February 2003  
 SUPERSEDING  
 MIL-PRF-19500/577A  
 3 July 1998

PERFORMANCE SPECIFICATION

SEMICONDUCTOR DEVICE, DIODE, SILICON, POWER RECTIFIER, FAST RECOVERY,  
 HIGH VOLTAGE, TYPES 1N6528 THROUGH 1N6535  
 JAN, JANTX, JANTXV, AND JANS

This specification is approved for use by all Departments and Agencies of the Department of Defense.

1. SCOPE

1.1 Scope. This specification covers the performance requirements for silicon, high voltage, fast recovery power rectifier diodes. Four levels of product assurance are provided for each device as specified in MIL-PRF-19500.

1.2 Physical dimensions. See figure 1 (similar to DO - 7).

1.3 Maximum ratings.

Types	V <sub>RWM</sub>	I <sub>FSM</sub> t <sub>p</sub> = 8.3 ms	I <sub>O</sub>		t <sub>rr</sub>	T <sub>J</sub> and T <sub>STG</sub>	R <sub>θJL</sub> L = .25
			T <sub>A</sub> = +55°C (1)	T <sub>A</sub> = +100°C (2)			
	V <sub>dc</sub>	A (pk)	mA dc	mA dc	ns	°C	°C/W
1N6528	1,500	10	250	125	70	-65 to +200	50
1N6529	2,000	10	250	125	70	-65 to +200	50
1N6530	2,500	8	100	50	70	-65 to +200	50
1N6531	3,000	8	100	50	70	-65 to +200	50
1N6532	4,000	4	50	25	70	-65 to +200	50
1N6533	5,000	4	50	25	70	-65 to +200	50
1N6534	7,500	2	25	12.5	70	-65 to +200	50
1N6535	10,000	2	25	12.5	70	-65 to +200	50

(1) Derate linearly for +55°C ≤ T<sub>A</sub> ≤ +100°C. I<sub>O</sub> at T<sub>A</sub> = +55°C to I<sub>O</sub> at T<sub>A</sub> = +100°C.

(2) Derate linearly for +100°C ≤ T<sub>A</sub> ≤ +175°C. I<sub>O</sub> at T<sub>A</sub> = +100°C to I<sub>O</sub> at T<sub>A</sub> = +0°C.

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Defense Supply Center, Columbus, ATTN: DSCC-VAC, P.O. Box 3990, Columbus, OH 43216-5000, by using the Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

AMSC N/A

FSC 5961

DISTRIBUTION STATEMENT A. Approved for public release; distribution is unlimited.

## 1.4 Primary electrical characteristics.

Types	$V_{RWM}$	$I_O$ $T_A = +55^\circ\text{C}$	$I_{R1}$ $T_A = +25^\circ\text{C}$	$V_{F1}$ at $I_O$	C at $V_R = 50\text{ V}$ $F_O = 1\text{ kHz}$	Barometric pressure (reduced)  t = 1 minute (minimum)
	<u>V dc</u>	<u>mA dc</u>	<u><math>\mu\text{A dc}</math></u>	<u>V (pk)</u>	<u>pF</u>	<u>mmHg</u>
1N6528	1,500	250	0.10	3.0	4.0	8
1N6529	2,000	250	0.10	3.0	4.0	8
1N6530	2,500	100	0.10	7.0	2.0	8
1N6531	3,000	100	0.10	7.0	2.0	8
1N6532	4,000	50	0.10	9.0	1.0	8
1N6533	5,000	50	0.10	9.0	1.0	8
1N6534	7,500	25	0.10	14.0	0.5	8
1N6535	10,000	25	0.10	14.0	0.5	8

## 2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3 and 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements documents cited in sections 3 and 4 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation (see 6.2).

## SPECIFICATION

## DEPARTMENT OF DEFENSE

MIL-PRF-19500 - Semiconductor Devices, General Specification for.

## STANDARD

## DEPARTMENT OF DEFENSE

MIL-STD-750 - Test Methods for Semiconductor Devices.

(Unless otherwise indicated, copies of the above specifications, standards, and handbooks are available from the Document Automation and Production Services (DAPS), Building 4D (DPM-DODSSP), 700 Robbins Avenue, Philadelphia, PA 19111-5094.)

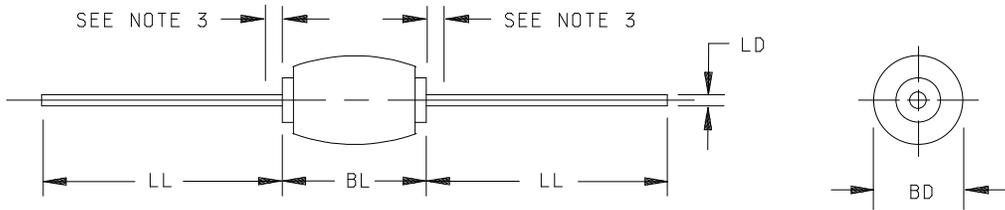


FIGURE 1. Physical dimensions (similar to DO - 7).

PIN	Dimensions															
	LD				BL				BD				LL			
	Inches		mm		Inches		mm		Inches		mm		Inches		mm	
	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
1N6528	.017	.023	0.43	0.58	0.140	0.200	3.56	5.08	.065	.125	1.65	3.18	1.0	1.3	25.4	33.0
1N6529	.017	.023	0.43	0.58	0.140	0.200	3.56	5.08	.065	.125	1.65	3.18	1.0	1.3	25.4	33.0
1N6530	.017	.023	0.43	0.58	0.160	0.220	4.06	5.59	.065	.125	1.65	3.18	1.0	1.3	25.4	33.0
1N6531	.017	.023	0.43	0.58	0.160	0.220	4.06	5.59	.065	.125	1.65	3.18	1.0	1.3	25.4	33.0
1N6532	.017	.023	0.43	0.58	0.180	0.240	4.57	6.10	.065	.125	1.65	3.18	1.0	1.3	25.4	33.0
1N6533	.017	.023	0.43	0.58	0.180	0.240	4.57	6.10	.065	.125	1.65	3.18	1.0	1.3	25.4	33.0
1N6534	.017	.023	0.43	0.58	0.240	0.300	6.10	7.62	.065	.125	1.65	3.18	1.0	1.3	25.4	33.0
1N6535	.017	.023	0.43	0.58	0.240	0.300	6.10	7.62	.065	.125	1.65	3.18	1.0	1.3	25.4	33.0

## NOTES:

1. Dimensions are in inches.
2. Metric equivalents are given for general information only.
3. The specified lead diameter applies in the zone between .05 inch (1.27 mm) from the body to the end of the lead. Outside of this zone lead shall not exceed the body diameter.
- \* 4. Dimensioning and tolerancing shall be in accordance with ASME Y14.5M.

FIGURE 1. Physical dimensions (similar to DO - 7) - Continued.

2.3 Order of precedence. In the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

### 3. REQUIREMENTS

3.1 General. The requirements for acquiring the product described herein shall consist of this document and MIL-PRF-19500.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see 4.2 and 6.3).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500.

3.4 Interface and physical dimensions. The interface and physical dimensions shall be as specified in MIL-PRF-19500 and on figure 1 (DO-7) herein.

3.4.1 Lead finish. Lead finish shall be solderable as defined in MIL-STD-750, MIL-PRF-19500, and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see 6.2).

\* 3.4.2 Diode construction. These devices shall be constructed utilizing non-cavity double plug construction with high temperature metallurgical bonding between both sides of the silicon die and terminal pins. Metallurgical bond shall be in accordance with the requirements of category I in MIL-PRF-19500.

3.5 Marking. Marking shall be in accordance with MIL-PRF-19500.

3.6 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in 1.3, 1.4, and table I herein.

3.7 Electrical test requirements. The electrical test requirements shall be the subgroups specified in 4.4.2 and 4.4.3 herein.

3.8 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

### 4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.4).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500 and table II herein.

4.3 Screening (JANS, JANTXV and JANTX levels only). Screening shall be in accordance with table IV of MIL-PRF-19500 and as specified herein. Specified electrical measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see appendix E, table IV of MIL-PRF-19500)	Measurement	
	JANS level	JANTX and JANTXV levels
(1)	Surge, see 4.3.2.	Surge, see 4.3.2.
9	$I_{R1}$ and $V_{F1}$	Not applicable
11	$I_{R1}$ and $V_{F1}$ ; $\Delta I_{R1}$ and $\Delta V_{F1}$ , see table III.	$I_{R1}$ and $V_{F1}$
12	See 4.3.1	See 4.3.1
13	Subgroups 2 and 3 of table I herein: $\Delta I_{R1}$ and $\Delta V_{F1}$ , see table III. $I_{R1}$ and $V_{F1}$	Subgroup 2 of table I herein: $\Delta I_{R1}$ and $\Delta V_{F1}$ , see table III. $I_{R1}$ and $V_{F1}$

(1) Surge screening shall be performed anytime after screen 3 and before screen 10.

4.3.1 Power burn-in conditions. Power burn-in conditions are as follows: Method 1038 of MIL-STD-750, condition B,  $T_A$  = room ambient as defined in the general requirements of 4 of MIL-STD-750;  $f$  (Hz)  $\geq$  60.

Types	$V_{RWM}$ (V dc)	$I_O$ (mA dc)
	<u>V dc</u>	
1N6528	1,000	250
1N6529	1,000	250
1N6530	1,000	100
1N6531	1,000	100
1N6532	1,000	50
1N6533	1,000	50
1N6534	1,000	25
1N6535	1,000	25

4.3.2 Surge screening. Method 4066 of MIL-STD-750,  $T_A$  = +25°C,  $V_{RWM}$  = 0. Six surges. Apply 20 x  $I_O$  rated at  $T_A$  of 55°C, 8.3 ms.

MIL-PRF-19500/577B

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with MIL-PRF-19500, and table I herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in appendix E, table VIa (JANS) and table VIb (JANTX and JANTXV) of MIL-PRF-19500. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of table III herein.

4.4.2.1 Group B inspection, appendix E, table VIa (JANS) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Conditions</u>
B3	4066	$I_O$ at $T_A = 55^\circ\text{C}$ , $I_{FSM} = \text{rated } I_{FSM}$ , see 1.3, one surge, 8.3 ms, $V_{RWM} = 0 \text{ V}$ .
B4	1037	See 4.3.1, $t_{on} = t_{off} = 3$ minutes minimum, 2,000 cycles.
B5	1027	$T_A = +150^\circ\text{C}$ minimum, $I_O = \text{rated } I_O$ (see 1.3) or adjust $I_O$ or $T_A$ as required to achieve $T_J = +275^\circ\text{C}$ for a minimum of 96 hours at $V_{RWM} = 1,000 \text{ V}$ .
B6	4081	$T_A = +25^\circ\text{C}$ ; $R_{\theta JL} = \text{rated } R_{\theta JL}$ (see 1.3).

4.4.2.2 Group B inspection, appendix E, table VIb (JANTX and JANTXV) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Conditions</u>
B2	4066	$I_O$ at $T_A = 55^\circ\text{C}$ , $I_{FSM} = \text{rated } I_{FSM}$ , see 1.3, one surge, 8.3 ms, $V_{RWM} = 0 \text{ V}$ .
B3	1027	$T_A = \text{room ambient}$ as defined in the general requirements of 4.5 of MIL-STD-750 minimum. $I_O = \text{rated } I_O$ (see 4.3.1 herein); adjust $I_O$ or $T_A$ as required to achieve $T_J = +125^\circ\text{C}$ , $V_{RWM} = 1,000 \text{ V}$ .
B5	4081	$T_A = +25^\circ\text{C}$ ; $R_{\theta JL} = \text{rated } R_{\theta JL}$ (see 1.3).

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in appendix E, table VII of MIL-PRF-19500. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of table III herein.

4.4.3.1 Group C inspection, appendix E, table VII of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Conditions</u>
C2	2036	Test condition A, weight = 5 lbs, $t = 30\text{s}$ .
C6	1026	$T_A = \text{room ambient}$ as defined in the general requirements of 4.5 of MIL-STD-750, $I_O = \text{rated } I_O$ (see 4.3.1); adjust $I_O$ or $T_A$ as required to achieve $T_J \leq +125^\circ\text{C}$ , $V_{RWM} = 1,000 \text{ V}$ .

4.5 Methods of inspection. Methods of inspection shall be specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

4.5.2 Inspection of conditions. Unless otherwise specified, all inspections shall be conducted at an ambient temperature,  $T_A = +25^\circ\text{C} \pm 3^\circ\text{C}$ .

4.5.3 Reverse-recovery time. The reverse recovery time shall be measured in the circuit of figure 2 or an equivalent circuit. The recovery conditions shall be 12.5 mA forward current to 25 mA reverse current. The reverse recovery time is defined as the time the rectifier begins to conduct in the reverse direction (crosses  $I = \text{zero}$ ) until the reverse current decays to -6.25 mA. The point of contact on the leads shall be no less than .375 inch (9.52 mm) from the diode body.

MIL-PRF-19500/577B

\* TABLE I. Group A inspection.

Inspection 1/	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical examination	2071					
<u>* Subgroup 2</u>						
Forward voltage	4011	$I_F = 25 \text{ mA}$	$V_{F1}$			V dc
1N6528, 1N6529					3.0	
1N6530, 1N6531					7.0	
1N6532, 1N6533					9.0	
1N6534, 1N6535					14.0	
Reverse current leakage	4016	DC method; $V_R = \text{rated } V_R \text{ (see 1.3)}$	$I_{R1}$		0.10	$\mu\text{A dc}$
Breakdown voltage	4021	$I_R = 50 \mu\text{A dc}$	$V_{(BR)R1}$			
1N6528				1,650		V dc
1N6529				2,200		V dc
1N6530				2,750		V dc
1N6531				3,300		V dc
1N6532				4,400		V dc
1N6533				5,500		V dc
1N6534				8,250		V dc
1N6535				11,000		V dc
<u>Subgroup 3</u>						
High temperature operation:		$T_A = 150^\circ\text{C}$				
Reverse current leakage	4016	DC method; $V_R = \text{rated } V_R \text{ (see 1.3)}$	$I_{R2}$		50	$\mu\text{A dc}$
Low temperature operation:		$T_A = -55^\circ\text{C}$				
Forward voltage	4011	$I_F = 25 \text{ mA}$	$V_{F2}$			V dc
1N6528, 1N6529					4.8	
1N6530, 1N6531					11.2	
1N6532, 1N6533					14.4	
1N6534, 1N6535					22.4	

See footnote at end of table.

MIL-PRF-19500/577B

\* TABLE I. Group A inspection - Continued.

Inspection 1/	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
* <u>Subgroup 3 - Continued</u> Breakdown voltage  1N6528 1N6529 1N6530 1N6531 1N6532 1N6533 1N6534 1N6535	4021	$I_R = 50 \mu\text{A dc}$	$V_{(BR)R2}$	1,500 2,000 2,500 3,000 4,000 5,000 7,500 10,000		V dc
<u>Subgroup 4</u> Reverse recovery		See 4.5.3 and figure 2	$t_{rr}$		70	ns
Capacitance  1N6528, 1N6529 1N6530, 1N6531 1N6532, 1N6533 1N6534, 1N6535	4001	$V_R = 50 \text{ V dc}, 1 \text{ kHz} \leq f \leq 100 \text{ kHz}$	C		4.0 2.0 1.0 0.5	pF
<u>Subgroups 5, 6 and 7</u> Not applicable						

1/ For sampling plan, see MIL-PRF-19500.

TABLE II. Group E inspection for (all quality levels) for qualification only.

Inspection	MIL-STD-750		Sampling plan
	Method	Conditions	
<u>Subgroup 1</u>			12 devices c = 0
Temperature shock	1051	500 cycles	
Electrical measurements		See table III, steps 1 and 2	
<u>Subgroup 2</u>			12 devices c = 0
Steady-state dc blocking life	1038	Condition A, t = 1,000 hours	
Electrical measurements		See table III, steps 1 and 2	
<u>Subgroup 3</u>			1 device, c = 0
Destructive physical analysis	2101		
<u>Subgroups 4 and 5</u>			
Not applicable			

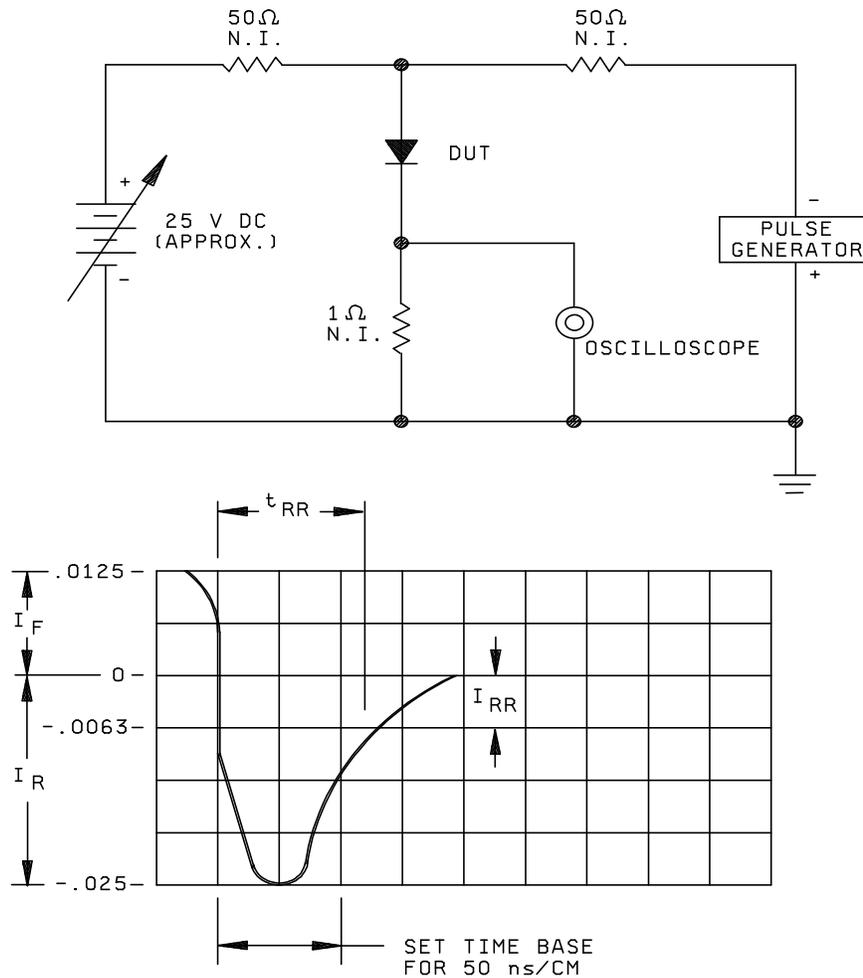
TABLE III. Groups A, B, C, and E electrical measurements. 1/ 2/ 3/

Step	Inspection	MIL-STD-750		Symbol	Limits		Unit
		Method	Conditions		Min	Max	
1.	Forward voltage	4011	Pulsed (see 4.5.1) $I_F = 25 \text{ mA}$ $t_p = 300 \mu\text{s}$ PPR = 60 Hz	$V_{F1}$			V (pk)
	1N6528, 1N6529					3.0	
	1N6530, 1N6531					7.0	
	1N6532, 1N6533					9.0	
	1N6534, 1N6535					14.0	
2.	Reverse current	4016	DC method $V_R = \text{rated } V_R$ (see 1.3)	$I_{R1}$		0.5	$\mu\text{A dc}$
3.	Reverse recovery time		See 4.5.3 and figure 2	$t_{rr}$		70	ns
4.	Capacitance	4001	$V_R = 50 \text{ V dc}$ ; $1 \text{ kHz} \leq f \leq 100 \text{ kHz}$	C			pF
	1N6528, 1N6529					4.0	
	1N6530, 1N6531					2.0	
	1N6532, 1N6533					1.0	
	1N6534, 1N6535					0.5	
5.	Forward voltage	4011	Pulsed (see 4.5.1) $I_F = 25 \text{ mA}$	$\Delta V_{F1}$			V (pk)
	1N6528, 1N6529					$\pm 0.2$	
	1N6530, 1N6531					$\pm 0.4$	
	1N6532, 1N6533					$\pm 0.8$	
	1N6534, 1N6535					$\pm 1.2$	
6.	Reverse current	4016	DC method	$\Delta I_{R1}$	50 nA or 100 percent of initial value, whichever is greater.		

See footnotes at top of next page.

TABLE III. Groups A, B, C, and E electrical measurements 1/ 2/ 3/ - Continued.

- 1/ The electrical measurements for appendix E, table VIa (JANS) of MIL-PRF-19500 are as follows:
  - a. Subgroup 3, see table III herein, steps 1, 2, 3, 4, 5, and 6.
  - b. Subgroup 4, see table III herein, steps 1, 2, 3, 4, 5, and 6.
  - c. Subgroup 5, see table III herein, steps 1, 2, 3, 4, 5, and 6.
- 2/ The electrical measurements for appendix E, table VIb (JANTX and JANTXV) of MIL-PRF-19500 are as follows:
  - a. Subgroup 2, see table III herein, steps 1, 2, and 3.
  - b. Subgroup 3, see table III herein, steps 1, 2, 3, and 4.
  - c. Subgroup 6, see table III herein, steps 1, 2, 3, and 4.
- 3/ The electrical measurements for appendix E, table VII of MIL-PRF-19500 are as follows:
  - a. Subgroup 2, see table III herein, steps 1, 2, 3, 4, 5, and 6 (JANS); and steps 2, and 3 (JANTX and JANTXV).
  - b. Subgroup 3, see table III herein, steps 1, 2 and 3.
  - c. Subgroup 6, see table III herein, steps 1, 2, 3, 4, 5, and 6 (JANS); and steps 2, 3, 4, and 5 (JANTX and JANTXV).



## NOTES:

1. Oscilloscope-rise time  $\leq 7$  ns; input impedance = 1 megohm; 22 pF.
2. Pulse generator - rise time  $\leq 10$  ns; source impedance 50 ohms.
3. Recovery time shall be measured on the above circuit and with equipment as shown. The pulse generator shall have a pulse repetition frequency of 1 kHz and a pulse width of 200 ns. Recovery conditions: 12.5 A forward current to .25 mA reverse current. Recovery time measured when rectifier recovers to 6.3 mA.

FIGURE 2. Reverse recovery time test circuit and characteristic nomograph.

## 5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activity within the Military Department or Defense Agency, or within the Military Department's System Command. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

## 6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory.)

6.1 Intended use. The notes specified in MIL-PRF-19500 are applicable to this specification.

6.2 Acquisition requirements. Acquisition documents must specify the following:

- a. Title, number, and date of this specification.
- b. Issue of DoDISS to be cited in the solicitation and if required, the specific issue of individual documents referenced (see 2.2.1).
- c. The lead finish as specified (see 3.4.1).
- d. Type designation and quality assurance level.
- e. Packaging requirements (see 5.1).

\* 6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturer's List QML No.19500 whether or not such products have actually been so listed by that date. The attention of the contractor (s) is called to these requirements. To assure eligibility of contract award or orders, manufacturers shall have the products covered by this specification tested. Information pertaining to qualification of products may be obtained from Defense Supply Center, Columbus, ATTN: DSCC-VQE, P.O. Box 3990, Columbus, OH 43216-5000.

6.4 Substitution information. Devices covered by this specification are substitutable for the manufacturers' and users' Part or Identifying Number (PIN). This information in no way implies that manufacturers' PIN's are suitable as a substitute for the military PIN.

PIN	Manufacturer's CAGE code	Manufacturer's and user's PIN
1N6528	53711 60211	8502234-215 RM115 M15FG M15UFG
1N6529	53711 49956 94117 60211	8502234-220 G339806 194087 RM116 RM135 RM140 M20FG M20UFG
1N6530	53711 60211	8502234-225 RM117 M25FG M25UFG
1N6531	53711  60211	4027428-103 4027428-113 8502234-230 4056502 RA352 RA643 RM118 RM123 M30FG M30UFG
1N6532	53711 23426 60211	8502234-240 28005-12 RM119 RM130 M40FG M40UFG

PIN	Manufacturer's CAGE code	Manufacturer's and user's PIN
1N6533	53711  60211	4027428-105 4027428-115 8502234-250 304-1-58A2 RA641 RA644 RM120 RM137 M50FG M50UFG
1N6534	53711  23426 60211	4027428-106 4027428-116 8502234-260 28005-7 RA642 RA645 RM121 RM131 M60FG M60UFG
1N6535	58260 53711  23426 60211  23426 60211	13084424 8502234-280 8502234-300 28005-8 M100FG RM122 RM109 RM132 M100UFG M80FG M80UFG

6.5 Changes from previous issue. The margins of this specification are marked with asterisks to indicate where changes from the previous issue were made. This was done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content irrespective of the marginal notations and relationship to the last previous issue.

Custodians:

Army - CR  
Navy - EC  
Air Force - 11  
NASA - NA  
DLA - CC

Preparing activity:

DLA - CC

(Project 5961-2669)

Review activities:

Army - AR, AV, MI, SM  
Air Force - 19, 99  
Navy - AS, MC, OS

## STANDARDIZATION DOCUMENT IMPROVEMENT PROPOSAL

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<b>I RECOMMEND A CHANGE:</b>	1. DOCUMENT NUMBER MIL-PRF-19500/577B	2. DOCUMENT DATE 19 February 2003
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3. **DOCUMENT TITLE**  
SEMICONDUCTOR DEVICE, DIODE, SILICON, POWER RECTIFIER, FAST RECOVERY, HIGH VOLTAGE, TYPES 1N6528 THROUGH 1N6535 JAN, JANTX, JANTXV, AND JANS

4. NATURE OF CHANGE (Identify paragraph number and include proposed rewrite, if possible. Attach extra sheets as needed.)

5. REASON FOR RECOMMENDATION

6. SUBMITTER

a. NAME (Last, First, Middle initial)	b. ORGANIZATION	
c. ADDRESS (Include Zip Code)	d. TELEPHONE (Include Area Code) COMMERCIAL DSN FAX EMAIL	7. DATE SUBMITTED

8. PREPARING ACTIVITY

a. Point of Contact Alan Barone	b. TELEPHONE Commercial      DSN      FAX      EMAIL 614-692-0510    850-0510    614-692-6939    alan.barone@dsccl.dla.mil		
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